

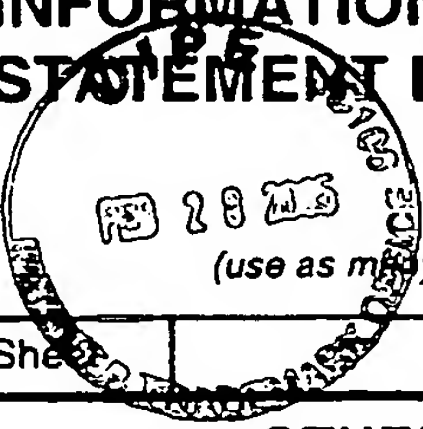
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Examiner Signature		Date Considered	Apr 14, 2005
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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<sup>1</sup> Unique citation designation number. <sup>2</sup> See attached Kinds of U.S. Patent Documents. <sup>3</sup> Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup> For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document.

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Substitute for Form 1449B/PTO  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>   (use as many sheets as necessary)		<b>Complete if Known</b>	
		Application Number	10/635,344
		Filing Date	August 6, 2003
		First Named Inventor	Alan E. Delahoy et al.
		Group Art Unit	1753
		Examiner Name	<del>Unknown</del> VerSteege
Sheet 1 of 2	Attorney Docket Number	ENPI 0101 PUS	
<b>OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS</b>			
Examiner Initials	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
SHV		"Deposition Schemes for Low Cost Transparent Conductors for Photovoltaics", A.E. Delahoy & M. Cherny, Mat. Res. Symp. Proc., Vol. 426, 1996, pgs. 467-477	
SHV		"High-Rate Low Kinetic Energy Gas-Flow-Sputtering System", K. Ishii, J. Vac. Sci. Technol. A, Vol. 7, No. 2, 1989, pgs. 256-258	
SHV		"Hollow Cathode Discharge Sputtering Device for Uniform Large Area Thin Film Deposition", H. Koch, J. Vac. Sci. Technol. A., Vol. 9, No. 4, 1991, pgs. 2374-2377	
SHV		"Zirconia Thin Film Deposition on Silicon by Reactive Gas Flow Sputtering: The Influence of Low Energy Particle Bombardment", T. Jung & A. Westphal, Mater. Sci. Eng., A140, 1991, pgs. 528-533	
SHV		"High Rate Deposition of Alumina Films by Reactive Gas Flow Sputtering", T. Jung & A. Westphal, Surf. Coat. Technol., 59, 1993, pgs. 171-176	
SHV		"Gas Flow Sputtering of Oxide Coatings: Practical Aspects of the Process", Th. Jung, T. Kälber, V.v.d. Heide, Surf. Coat. Technol., 86-87, 1996, pgs. 218-224	
SHV		"New DC Sputter Sources for the Large Scale Deposition of Oxide Films", M. Höfer, A. Jung, T. Jung, H.-U. Kricheldorf & F. Schmidt, Proc. 43 <sup>rd</sup> SVC Annual Tech. Conf., 2000, pgs. 287-292	

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